

BS170 / MMBF170

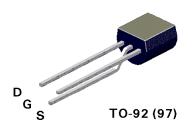
N-Channel Enhancement Mode Field Effect Transistor

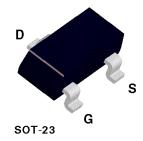
General Description

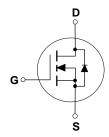
These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- High density cell design for low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.







Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
V _{DSS}	Drain-Source Voltage		V	
$V_{\rm DGR}$	Drain-Gate Voltage ($R_{GS} \le 1M\Omega$)		60	V
V _{GSS}	Gate-Source Voltage	Ė	± 20	V
D	Drain Current - Continuous	500	500	mA
	- Pulsed	1200	800	
P _D	Maximum Power Dissipation	830	300	mW
	Derate Above 25°C	6.6	2.4	mW/°C
T_J , T_{STG}	Operating and Storage Temperature Range	-55	°C	
T _L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	:	°C	
THERMA	L CHARACTERISTICS			
R _{eJA}	Thermal Resistacne, Junction-to-Ambient	150	417	°C/W

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Symbol	Parameter	Conditions	Туре	Min	Тур	Max	Units
OFF CHA	RACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 100 \mu\text{A}$	All	60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$	All			0.5	μΑ
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 15 \text{ V}, V_{DS} = 0 \text{ V}$	All			10	nA
ON CHAR	ACTERISTICS (Note 1)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	All	8.0	2.1	3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 200 \text{ mA}$	All		1.2	5	Ω
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 200 \text{ mA}$	BS170		320		mS
		$V_{DS} \ge 2 V_{DS(on)}, I_{D} = 200 \text{ mA}$	MMBF170		320		
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, \ V_{GS} = 0 \text{ V},$	All		24	40	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	All		17	30	pF
C _{rss}	Reverse Transfer Capacitance		All		7	10	pF
SWITCHI	NG CHARACTERISTICS (Note 1)						
t _{on}	Turn-On Time	$V_{DD} = 25 \text{ V}, \ I_{D} = 200 \text{ m A}, \ V_{GS} = 10 \text{ V}, R_{GEN} = 25 \Omega$	BS170			10	ns
		V_{DD} = 25 V, I_{D} = 500 mA, V_{GS} = 10 V, R_{GEN} = 50 Ω	MMBF170			10	
t _{off}	Turn-Off Time	$V_{DD} = 25 \text{ V}, \ I_{D} = 200 \text{ m A}, \ V_{GS} = 10 \text{ V}, \ R_{GEN} = 25 \Omega$	BS170			10	ns
		$V_{DD} = 25 \text{ V}, \ I_{D} = 500 \text{ mA}, \ V_{GS} = 10 \text{ V}, \ R_{GFN} = 50 \Omega$	MMBF170			10	

Note:
1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

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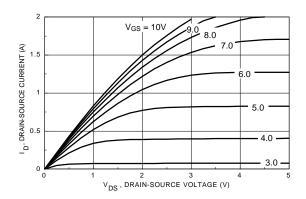


Figure 1. On-Region Characteristics.

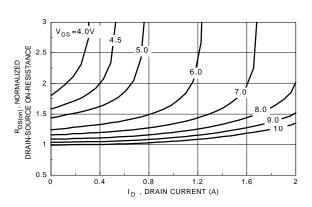


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

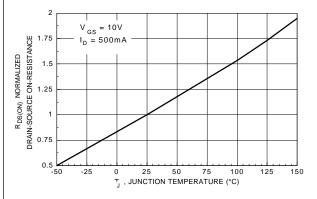


Figure 3. On-Resistance Variation with Temperature.

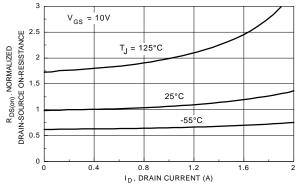


Figure 4. On-Resistance Variation with Drain Current and Temperature.

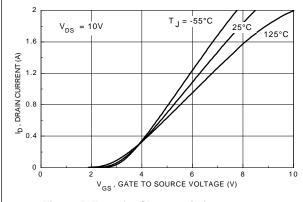


Figure 5. Transfer Characteristics.

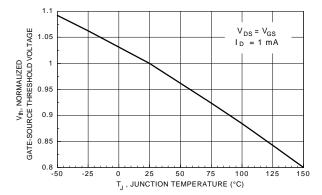


Figure 6. Gate Threshold Variation with Temperature.

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Typical Electrical Characteristics (continued)

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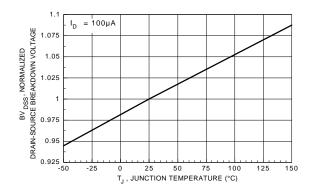


Figure 7. Breakdown Voltage Variation with Temperature.

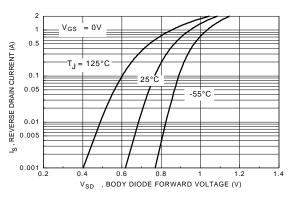


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

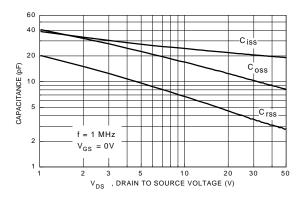


Figure 9. Capacitance Characteristics.

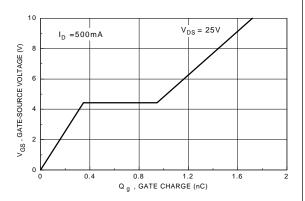


Figure 10. Gate Charge Characteristics.

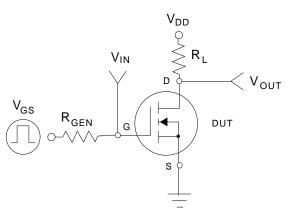


Figure 11. Switching Test Circuit.

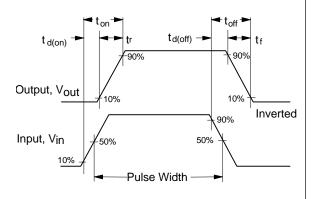
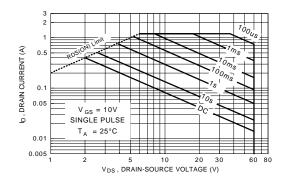


Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)



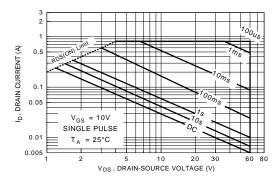


Figure 13. BS170 Maximum Safe Operating Area.

Figure 14. MMBF170 Maximum Safe Operating Area.

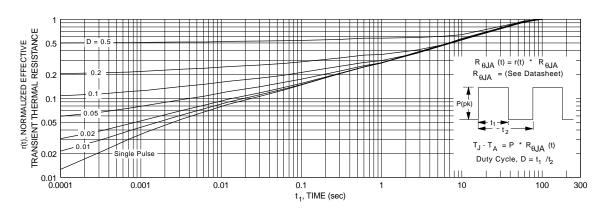


Figure 15. TO-92, BS170 Transient Thermal Response Curve.

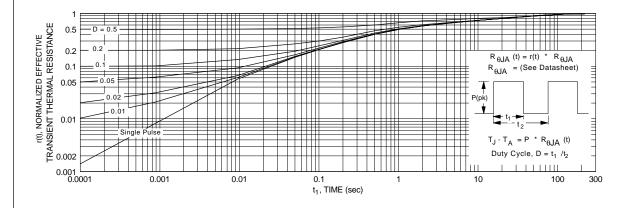
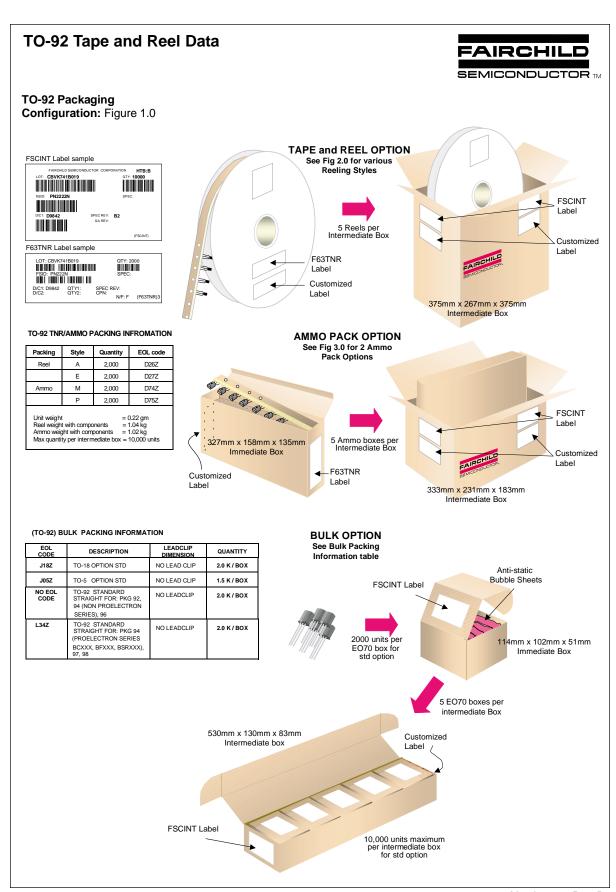


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve.

BS170 Rev. C / MMBF170 Rev. D

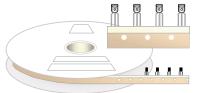


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



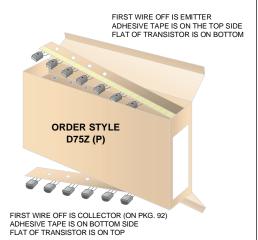
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

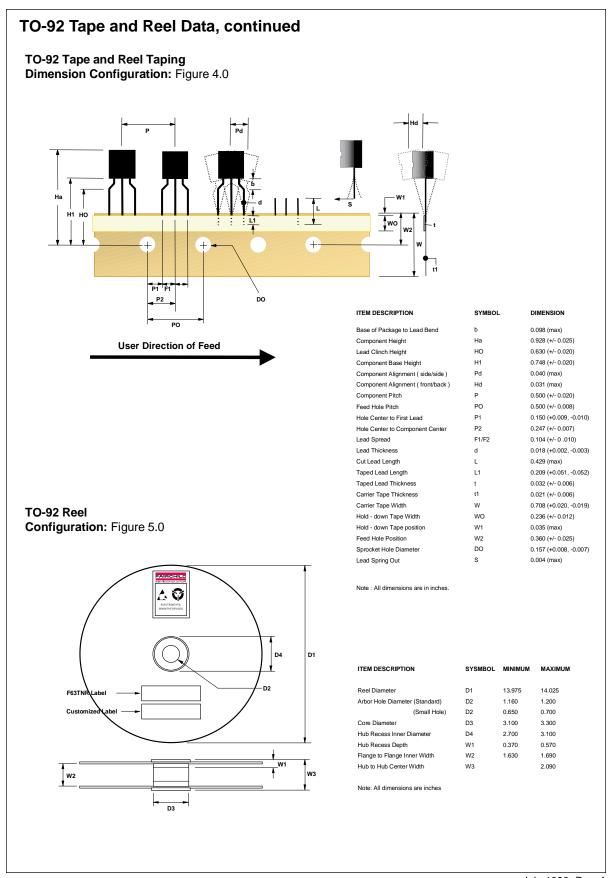
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





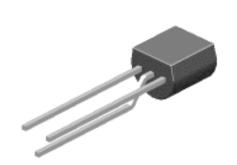
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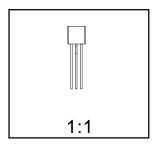


TO-92 Package Dimensions



TO-92; TO-18 Reverse Lead Form (J35Z Option) (FS PKG Code 92, 94, 96)

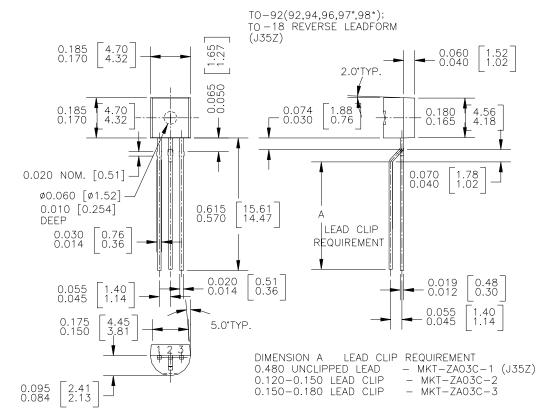




Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

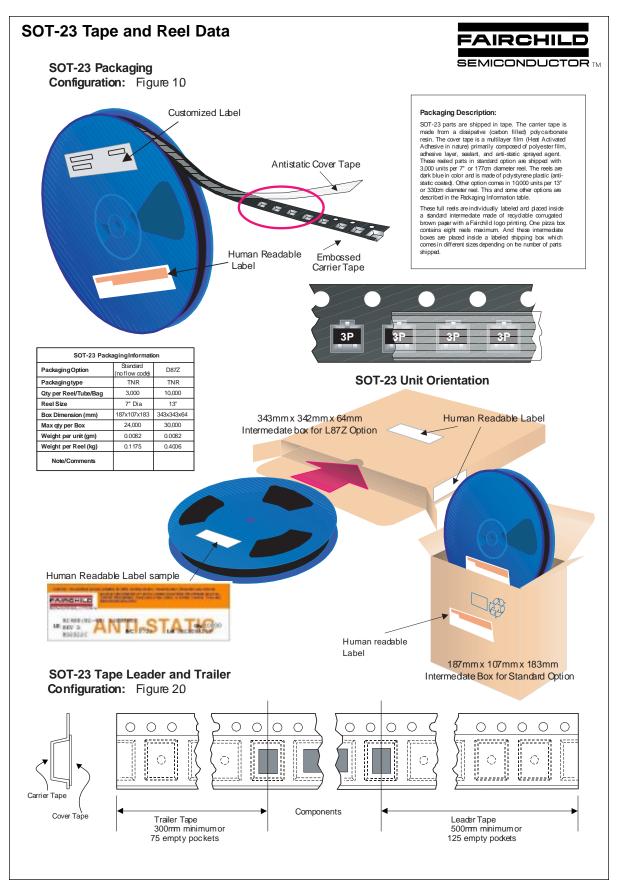
Part Weight per unit (gram): 0.22



Note: All package 97 or 98 transistors are leadformed to this configuration prior to bulk shipment. Order L34Z option if in-line leads are preferred on package 97 or 98.

January 2000, Rev. B

^{*} Standard Option on 97 & 98 package code

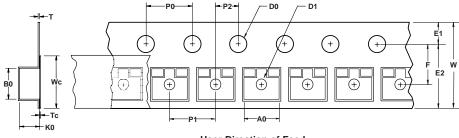


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SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



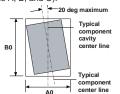
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



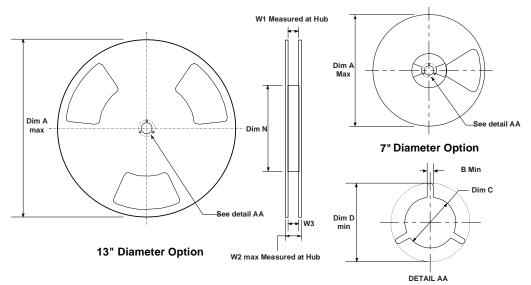
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

SOT-23 Reel Configuration: Figure 4.0

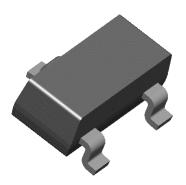


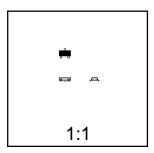
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SOT-23 Package Dimensions



SOT-23 (FS PKG Code 49)

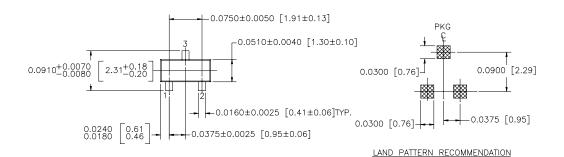


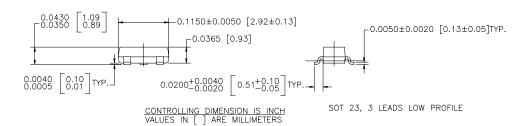


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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DOME™ ISOPLANAR™ Quiet Series™

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Rev. G